

Amendments to the Claims

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims

1. (Currently amended) A method for processing a semiconductor topography, comprising polishing the topography with a polishing solution on a polishing pad without adding water to the polishing solution that is on the polishing pad during the polishing, and wherein water is not added to the polishing solution before the polishing solution is deposited on the polishing pad.
2. (Previously Presented) The method of claim 1, wherein a pH of the polishing solution on the polishing pad is substantially uniform during the polishing.
3. (Previously Presented) The method of claim 1, wherein a pH of the polishing solution on the polishing pad varies by less than about 2.5 during the polishing.
4. (Previously Presented) The method of claim 1, wherein a pH of the polishing solution on the polishing pad varies by less than about 30 % during the polishing.
5. (Original) The method of claim 1, wherein subsequent to the polishing, a substantial amount of residual slurry particles are present on the topography.
6. (Original) The method of claim 1, wherein subsequent to the polishing, the topography is substantially free of agglomerated slurry particles.
7. (Original) The method of claim 1, wherein subsequent to the polishing, the topography is substantially free of slurry particles having a particle size of greater than about 10 μm .
8. - 12. (Canceled)

13. (Currently Amended) A method for processing a semiconductor topography, comprising;

polishing the semiconductor topography with a polishing pad while simultaneously depositing a polishing solution on the polishing pad;

terminating the deposition of the polishing solution on the polishing pad;

subsequently polishing the semiconductor topography with the polishing pad having residual amounts of the polishing solution thereon; and

depositing water on the polishing pad in a plurality of dispense intervals during the step of subsequently polishing of the semiconductor topography to reduce a rate of change of a pH of the residual amounts of polishing solution on the topography polishing pad, wherein the step of depositing the water is conducted subsequent to starting the step of subsequently polishing the semiconductor topography.

14. (Original) The method of claim 13, wherein each of the plurality of dispense intervals comprise a dispense time of less than about 30 seconds.

15. (Original) The method of claim 13, wherein one or more of the plurality of dispense intervals comprise a dispense time of less than about 3 seconds.

16. (Original) The method of claim 13, wherein the polishing solution comprises slurry present on the topography prior to the polishing.

17. (Original) The method of claim 13, wherein additional polishing solution is not deposited on the polishing pad during the polishing.

18. (Original) The method of claim 13, wherein the topography comprises an upper layer of oxide formed across the topography, and wherein the oxide is substantially planar subsequent to the polishing.

19. (Previously Presented) A method for processing a semiconductor topography, comprising:

polishing the topography with a polishing solution on a primary polishing pad during a primary polishing step without adding water to the polishing solution that is on the primary polishing pad during the polishing; and

polishing the topography on a final polishing pad during a final polishing step, comprising depositing water on the final polishing pad in a plurality of dispense intervals to reduce a rate of change of a pH of a polishing solution on the topography.

20. (Original) The method of claim 19, further comprising transferring the topography from the primary polishing pad to the final polishing pad subsequent to the primary polishing step, wherein a substantial amount of residual slurry particles are present on the topography during the transferring.

21. (Canceled)

22. (Previously Presented) The method of claim 1, wherein a pH of the polishing solution is approximately equal to a pH of the polishing solution as commercially supplied.

23. (Currently Amended) The method of claim ~~1~~13, wherein the water has a pH of about 7.

24. (Previously Presented) The method of claim 1, wherein the polishing is a primary polishing step, wherein subsequent to the polishing, a substantial amount of residual slurry particles are present on the topography, and wherein the method further comprises transferring the topography to a final polishing step with the residual slurry particles present on the topography.

25. (Previously Presented) The method of claim 1, wherein subsequent to the polishing, a substantial amount of residual slurry particles are present on the topography, and wherein the method further comprises transferring the topography to a cleaning step with the residual slurry particles present on the topography.